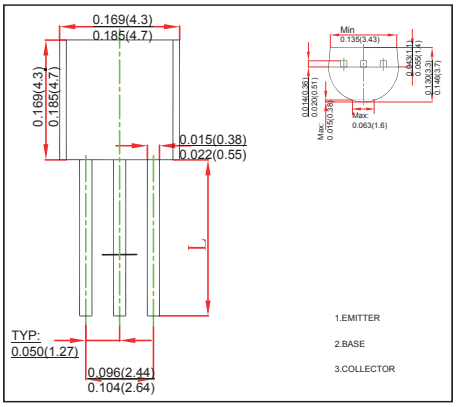
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Low collector Saturation Voltage:Vce(sat)=-0.3V(Max)
- Low Output Capacitance:Cob=4pF(Typ.)
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.15	A
Collector Power Dissipation	P_D	625	mW
Thermal Resistance from Junction to Ambient	$R_{K\,JA}$	200	℃ /W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55~+150	℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unia
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{EB}=-5V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-2mA	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA,I_B=-10mA			-0.3	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-1mA	80			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		4	7	pF
Noise figure	NF	V_{CE}=-6V,I_C=-0.1mA,f=1KHz,R_S=10KΩ			10	dB